

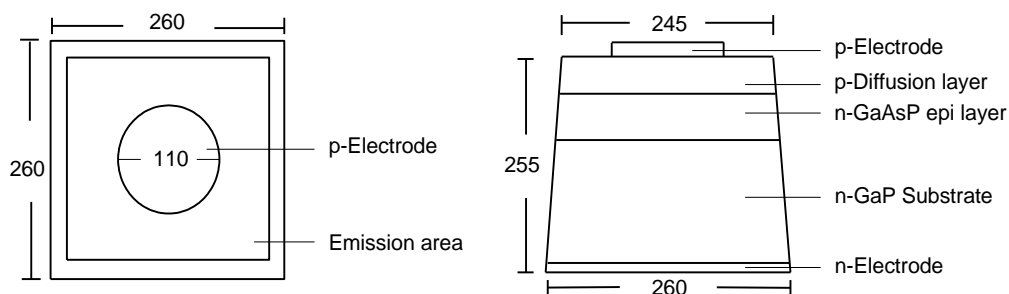
■ Features :

- GaAsP/GaP Epi Wafer

■ Typical Applications :

- Lamp
- SMD
- Display
- Dot Matrix

■ Outline Dimensions : (Unit:um)



■ Physical Structure :

| | | |
|-------------------|-----------------------|--------------------------|
| Chip dimension | Chip size | 260 um x 260 um |
| | Thickness | 255 um |
| | Emission area | 245 um |
| | Bonding pad | 110 um |
| Electrode | Top: P (anode) | Aluminum (Gold optional) |
| | Backside: N (cathode) | Gold alloy |
| Surface condition | Not frosted | |

■ Electro-Optical Characteristics : (Ta = 25°C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------|------------------|-----------------------|------|------|------|------|
| Forward Voltage | V_F | $I_F = 20 \text{ mA}$ | - | 2.00 | 2.60 | V |
| Reverse Current | I_R | $V_R = 5 \text{ V}$ | - | - | 10 | uA |
| Wavelength | λ_P | $I_F = 20 \text{ mA}$ | - | 632 | - | nm |
| | Hue | | - | 620 | - | |
| Spectral width at half height | $\Delta \lambda$ | $I_F = 20 \text{ mA}$ | - | 35 | - | nm |
| Luminous Intensity | I_V | $I_F = 20 \text{ mA}$ | 6.0 | - | - | mcd |

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

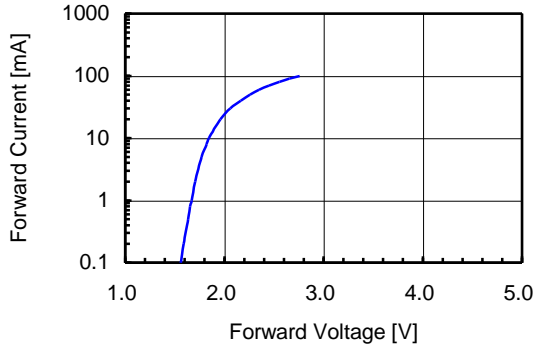


Fig 2. Relative Intensity vs. Forward Current

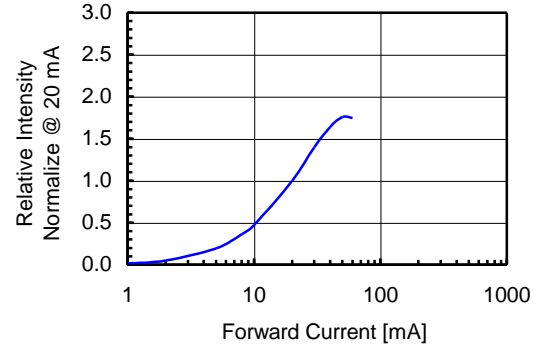


Fig 3. Forward Voltage vs. Temperature

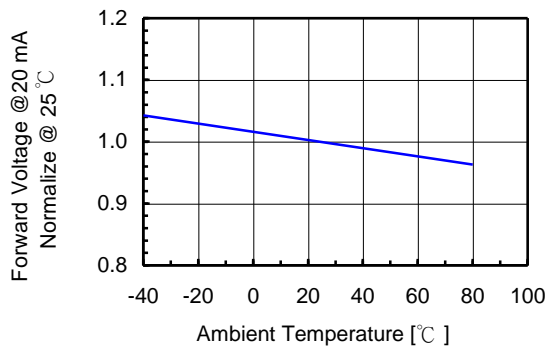


Fig 4. Relative Intensity vs. Temperature

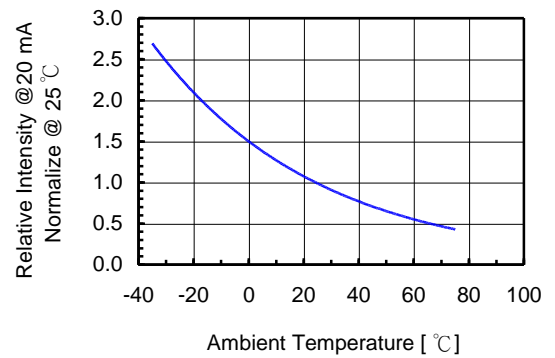


Fig 5. Relative Intensity vs. Wavelength

